NCE15H10D

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE15H10D uses advanced trench technology and design to provide excellent $R_{\rm DS(ON)}$ with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.

General Features

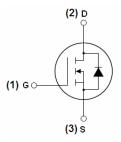
- V_{DS} =150V, I_{D} =100A $R_{DS(ON)}$ <11mΩ @ V_{GS} =10V (Typ:9.5mΩ)
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Special designed for convertors and power controls
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% ΔVds TESTED!



Schematic diagram



Marking and pin assignment



TO-263-2L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE15H10D	NCE15H10D	TO-263-2L	-	-	-

Absolute Maximum Ratings (T_C =25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	150	V
Gate-Source Voltage	V _G s	±20	V
Drain Current-Continuous	I _D	100	А
Drain Current-Continuous(T _C =100°C)	I _D (100℃)	70	Α
Pulsed Drain Current	I _{DM}	390	Α
Maximum Power Dissipation	P _D	370	W
Derating factor		2.47	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	1600	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	$^{\circ}$

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Thermal Characteristic

Thermal Resistance,Junction-to-Cas ^{e(Note 2)}	$R_{ heta JC}$	0.41	°C/W	
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Electrical Characteristics (T_C=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	150	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =150V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V_{DS} = V_{GS} , I_D =250 μ A	2.5	3.4	4.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =40A	-	9.5	11	mΩ
Forward Transconductance	g FS	V _{DS} =25V,I _D =40A	100	-	-	S
Dynamic Characteristics (Note4)	•					
Input Capacitance	C _{lss}	., .=.,,	-	7500	-	PF
Output Capacitance	C _{oss}	V_{DS} =25V, V_{GS} =0V, F=1.0MHz	-	640	-	PF
Reverse Transfer Capacitance	C _{rss}	F-1.UIVITZ	-	426	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	32.5	-	nS
Turn-on Rise Time	t _r	VDD=75V,ID=2A,RL=15Ω	-	30	-	nS
Turn-Off Delay Time	t _{d(off)}	,RG=2.5Ω,VGS=10V	-	113	-	nS
Turn-Off Fall Time	t _f		-	48	-	nS
Total Gate Charge	Qg	\/ -75\/ -404	-	138	-	nC
Gate-Source Charge	Q _{gs}	V_{DS} =75V, I_{D} =40A, V_{GS} =10V	-	46	-	nC
Gate-Drain Charge	Q_{gd}	V _{GS} -10V	-	39	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =40A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	100	Α
Reverse Recovery Time	t _{rr}	Tj=25℃,I _F =40A,di/dt=100A/μs	-	45		nS
Reverse Recovery Charge	Qrr	(Note3)	-	80		nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+L			LS+LD)	

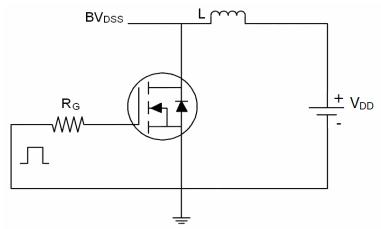
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- **5.** EAS condition: Tj=25 $^{\circ}\text{C}$,VDD=50V,VG=10V,L=0.5mH,Rg=25 Ω

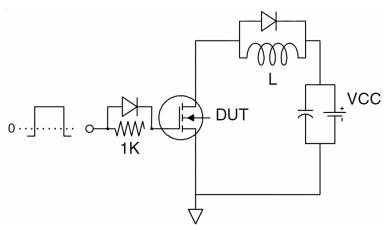
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Test circuit

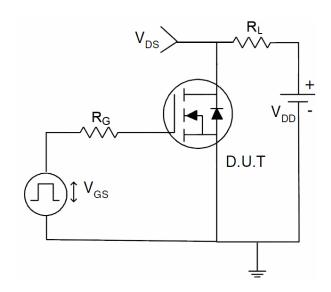
1) E_{AS} test Circuits



2) Gate charge test Circuit:



3) Switch Time Test Circuit:





Typical Electrical and Thermal Characteristics (Curves)

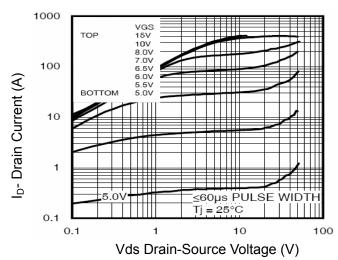


Figure 1 Output Characteristics

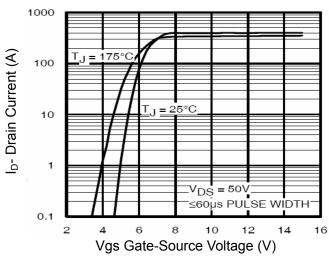


Figure 2 Transfer Characteristics

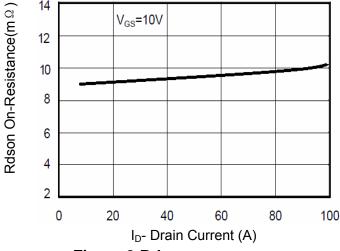


Figure 3 Rdson- Drain Current

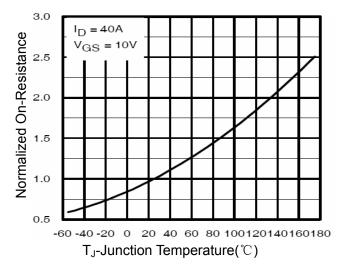


Figure 4 Rdson-JunctionTemperature

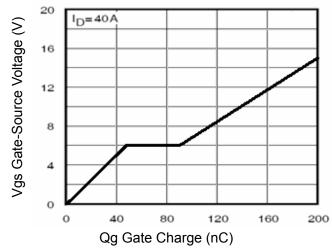


Figure 5 Gate Charge

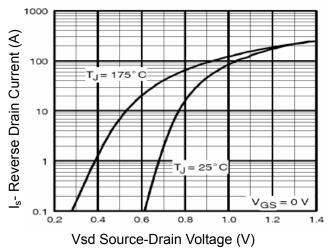


Figure 6 Source- Drain Diode Forward



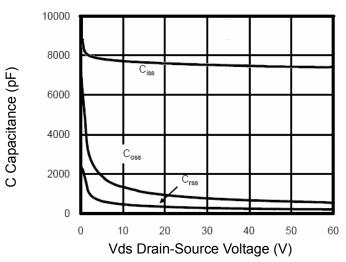


Figure 7 Capacitance vs Vds

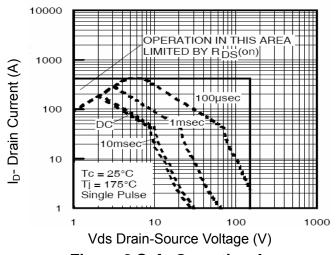


Figure 8 Safe Operation Area

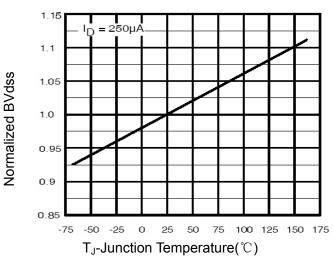


Figure 9 BV_{DSS} vs Junction Temperature

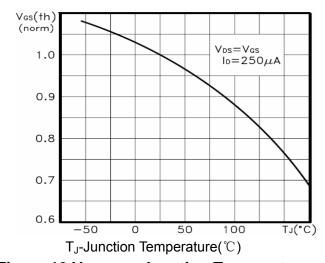


Figure 10 V_{GS(th)} vs Junction Temperature

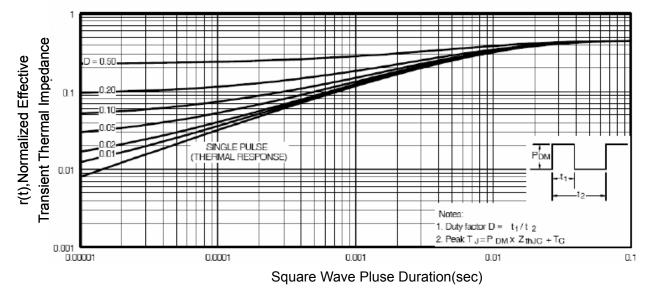
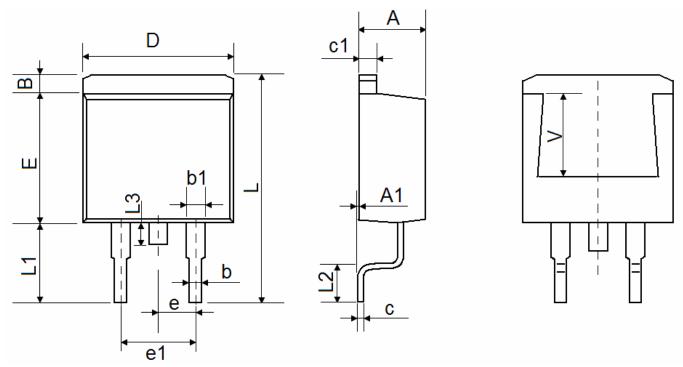


Figure 11 Normalized Maximum Transient Thermal Impedance



TO-263-2L Package Information



Complete	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.470	4.670	0.176	0.184	
A1	0.000	0.150	0.000	0.006	
В	1.170	1.370	0.046	0.054	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.310	0.530	0.012	0.021	
c1	1.170	1.370	0.046	0.054	
D	10.010	10.310	0.394	0.406	
E	8.500	8.900	0.335	0.350	
е	2.540	TYP.	0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
L	15.050	15.450	0.593	0.608	
L1	5.080	5.480	0.200	0.216	
L2	2.340	2.740	0.092	0.108	
L3	1.300	1.700	0.051	0.067	
V	5.60	5.600 REF 0.220 REF			



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